

DESCRIPTION

The MXN30D12M uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

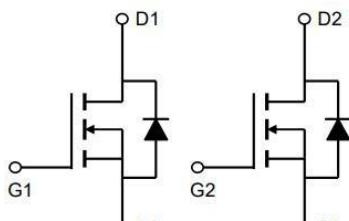
GENERAL FEATURES

- $V_{DS}=30V$, $I_D=12A$
- $R_{DS(ON)}(\text{Typ.})=15.5\text{m}\Omega$ @ $V_{GS}=4.5V$
- $R_{DS(ON)}(\text{Typ.})=12\text{m}\Omega$ @ $V_{GS}=10V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

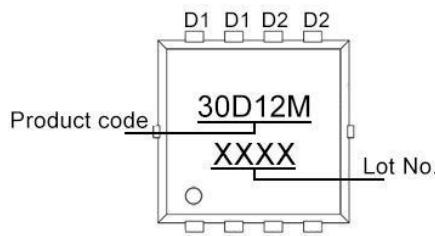
APPLICATION

- PWM applications
- Load switch
- Power management

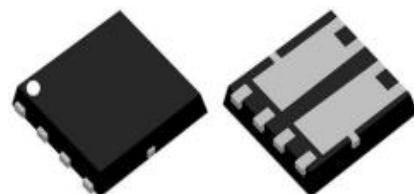
PINOUT



Schematic diagram



Marking and Pin Assignment



PDFN3.3X3.3-8L Top View

ORDERING INFORMATION

Part Number	Storage Temperature	Package	Devices Per Reel
MXN30D12M	-55°C to 150°C	PDFN3.3X3.3-8L	5000

ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	12	A
Drain Current-Continuous($T_C=70^\circ C$)	I_D	9	A
Pulsed Drain Current ^(Note 1)	I_{DM}	48	A
Single Pulse Avalanche Energy($L=0.1\text{mH}$)	E_{AS}	24	mJ
Maximum Power Dissipation	P_D	20.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL CHARACTERISTIC

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JC}$	6	°C/W
---	-----------------	---	------

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.


ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
-----------	--------	------------	-----	-----	-----	------

Off Characteristics

Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA

On Characteristics^(Note 3)

Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	1.8	2.5	V
Drain-Source On-State Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=6\text{A}$	-	15.5	20	$\text{m}\Omega$
		$V_{\text{GS}}=10\text{V}, I_{\text{D}}=8\text{A}$	-	12	14	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}}=5\text{V}, I_{\text{D}}=8\text{A}$	-	24	-	S

Dynamic Characteristics^(Note 4)

Input Capacitance	C_{iss}	$V_{\text{DS}}=15\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	840	-	pF
Output Capacitance	C_{oss}		-	120	-	pF
Reverse Transfer Capacitance	C_{rss}		-	85	-	pF

Switching Characteristics^(Note 4)

Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=15\text{V}, I_{\text{D}}=2\text{A}, R_{\text{L}}=1\Omega, V_{\text{GS}}=10\text{V}, R_{\text{G}}=3\Omega$	-	4.2	-	nS
Turn-on Rise Time	t_{r}		-	8.2	-	nS
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	31	-	nS
Turn-Off Fall Time	t_{f}		-	4	-	nS
Total Gate Charge	Q_{g}	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=6\text{A}, V_{\text{GS}}=10\text{V}$	-	14	-	nC
Gate-Source Charge	Q_{gs}		-	2.4	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC

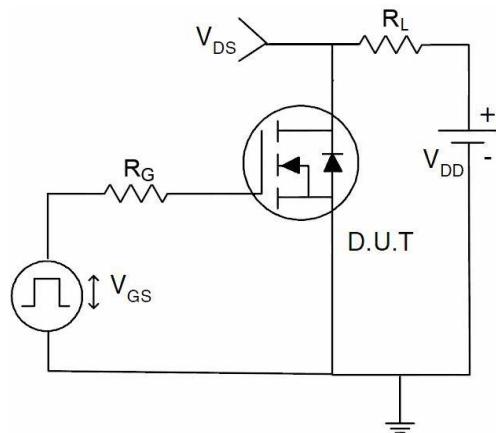
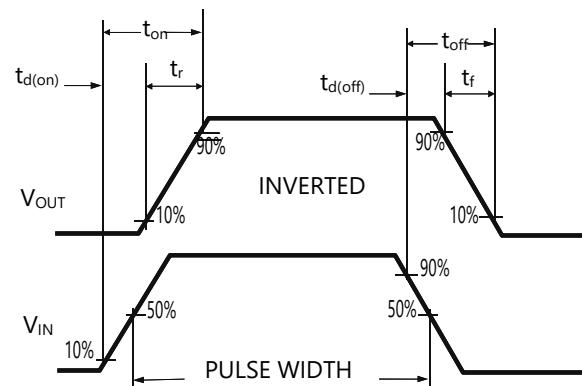
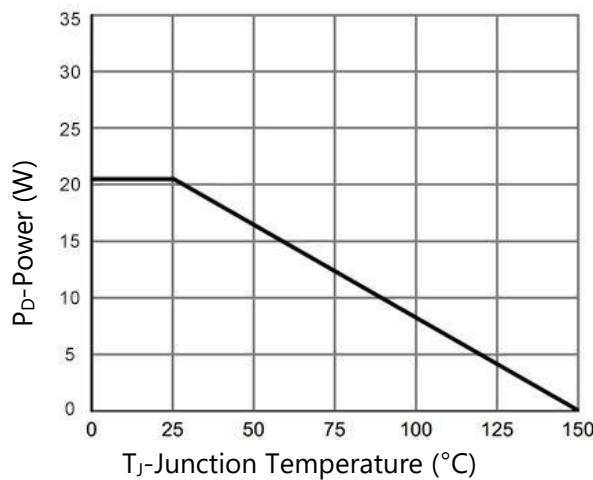
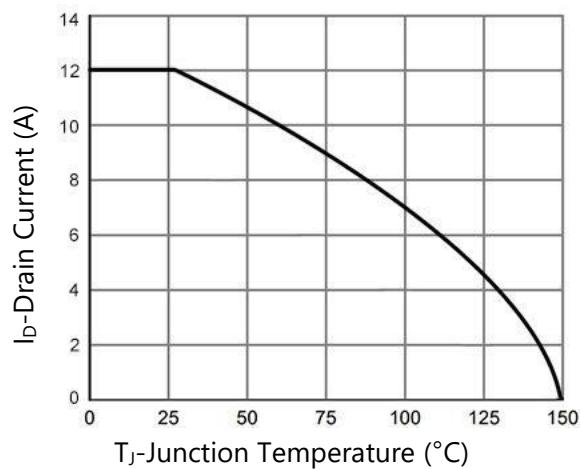
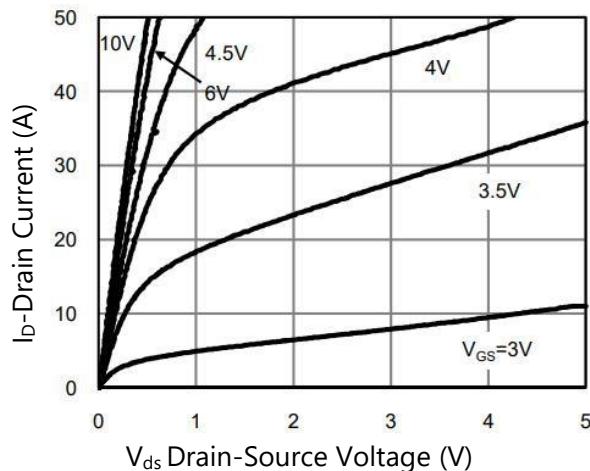
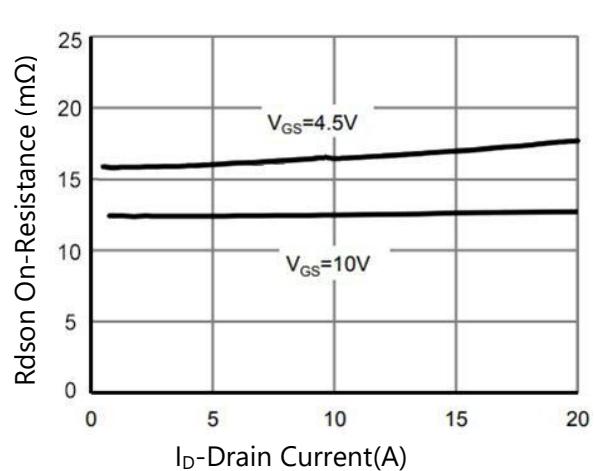
Drain-Source Diode Characteristics

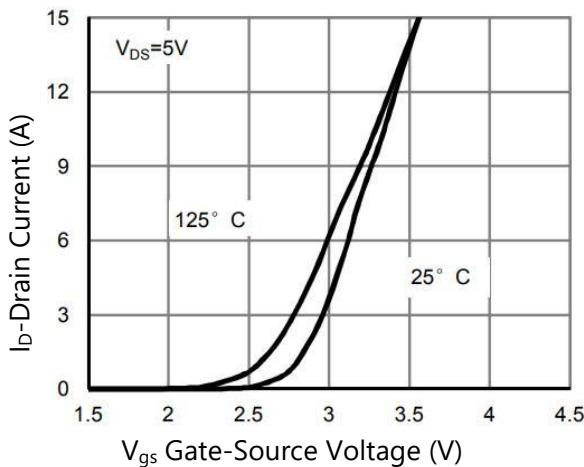
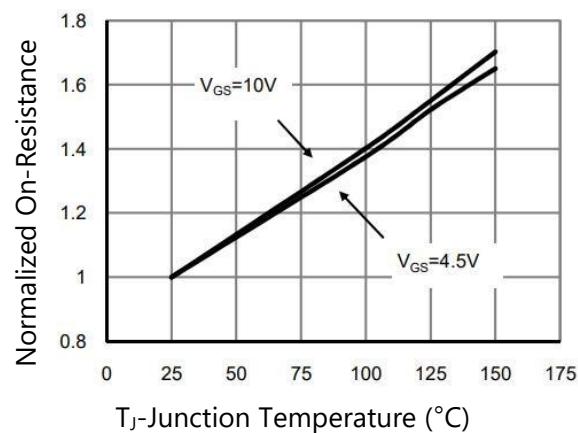
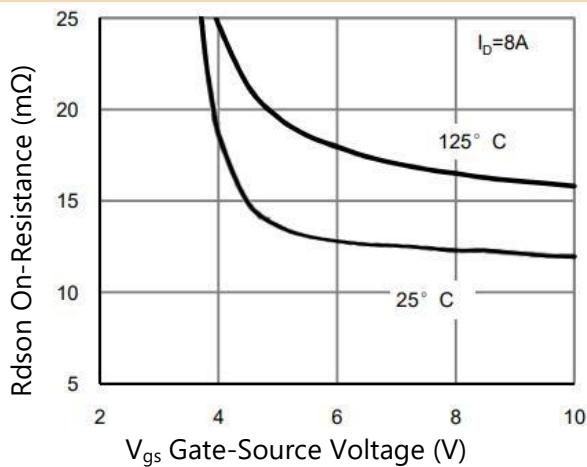
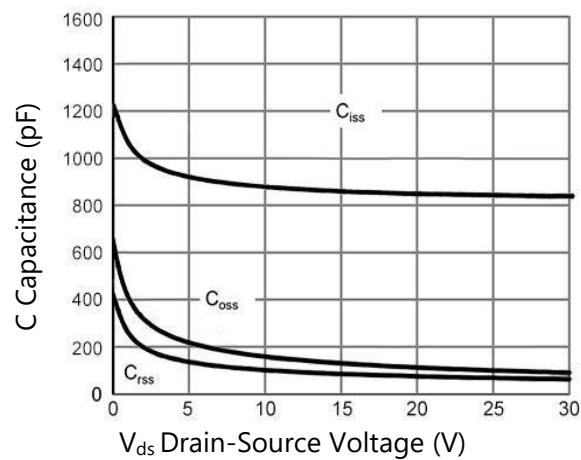
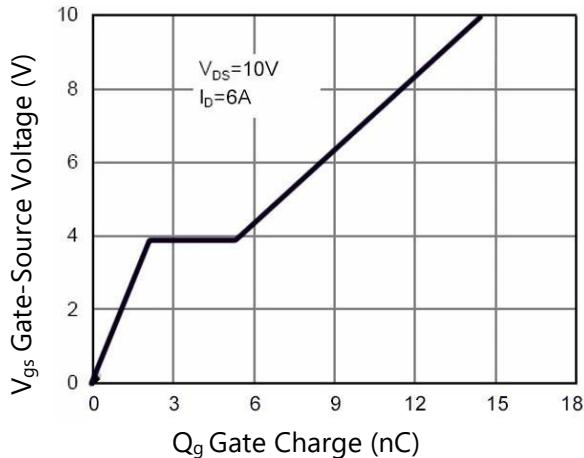
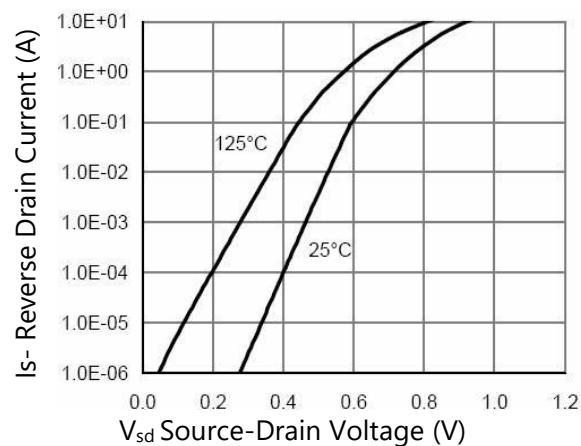
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=1\text{A}$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_{S}		-	-	8	A

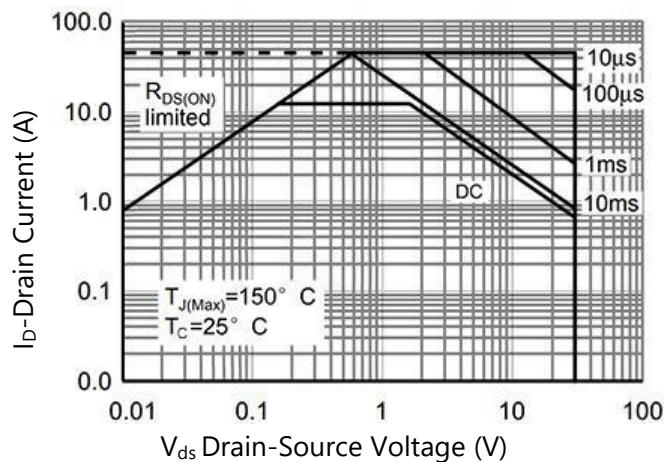
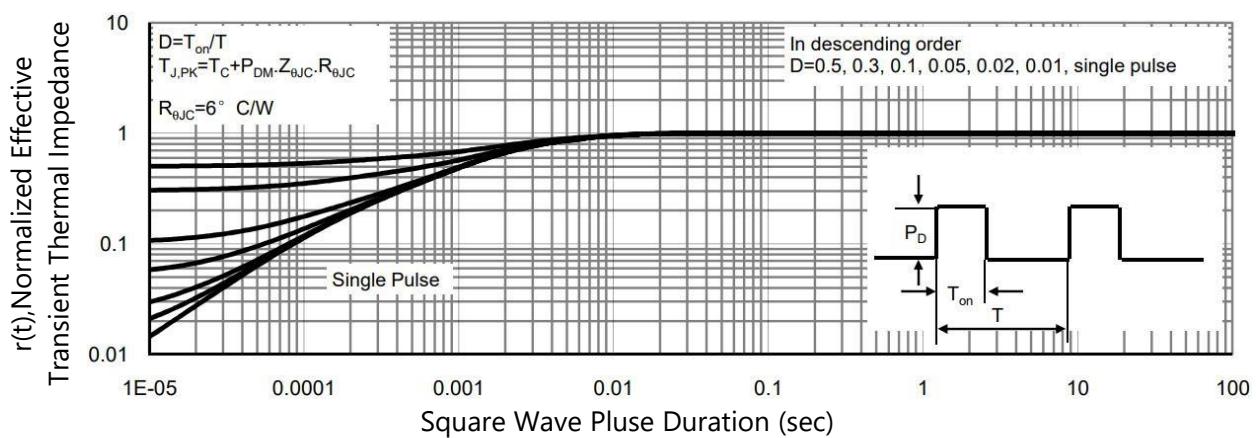
Note 2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

Note 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

Note 4. Guaranteed by design, not subject to product.

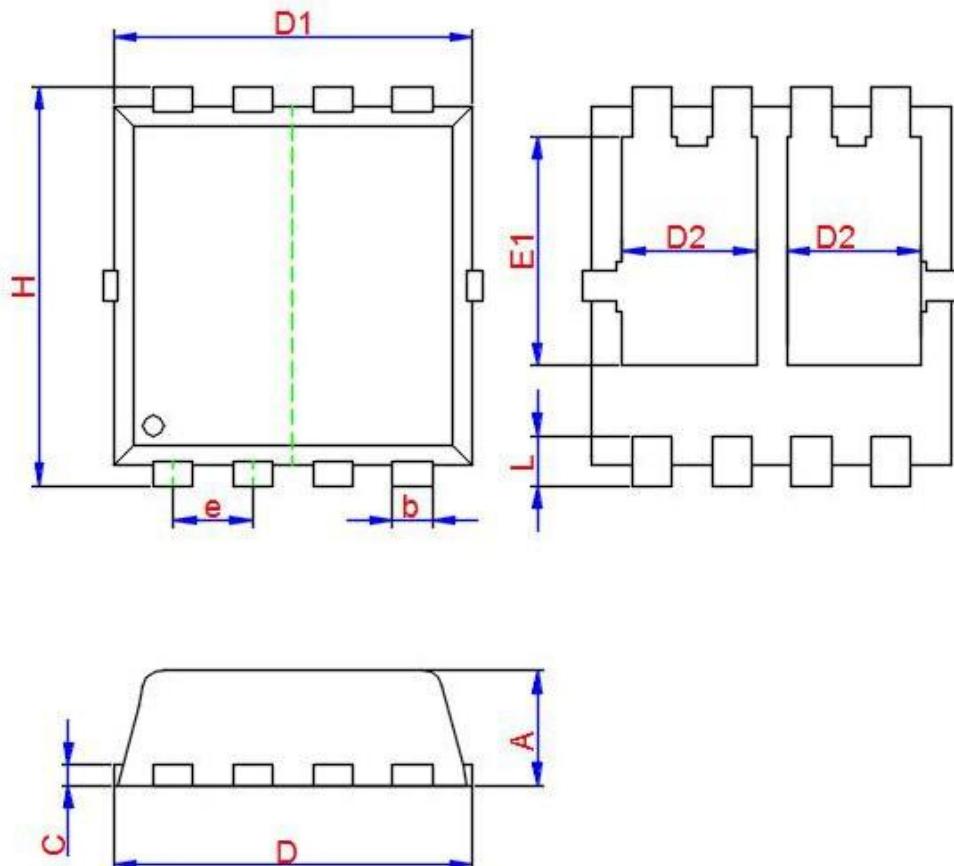

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 1. Switching Test Circuit

Figure 2. Switching Waveform

Figure 3. Power De-rating

Figure 4. Drain Current

Figure 5. Output Characteristics

Figure 6. Rdson vs Drain Current



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 7. Transfer Characteristics

Figure 8. $R_{DS(on)}$ vs Junction Temperature

Figure 9. $R_{DS(on)}$ vs V_{GS}

Figure 10. Capacitance vs V_{ds}

Figure 11. Gate Charge

Figure 12. Source- Drain Diode Forward



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS
Figure 13 Safe Operation Area

Figure 14. Normalized Maximum Transient Thermal Impedance


PACKAGE INFORMATION

TSSOP-8



SYMBOLS	DIMENSIONS IN MILLIMETERS		
	MIN	TYP	MAX
A	0.675	0.775	0.875
b		0.030(TYP)	
C		0.152(TYP)	
D	3.100	3.300	3.500
D1	3.050	3.150	3.250
D2	0.835	1.035	1.235
e		0.650(TYP)	
E1	1.530	1.730	1.930
H	3.150	3.350	3.550
L	0.280	0.380	0.480